

## Anisotropic Expansion and High Rate Discharge Performance of V-doped MnO<sub>2</sub> for Li/MnO<sub>2</sub> Primary Battery

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V-doped MnO<sub>2</sub> (VHEMD) has been prepared by thermally treating the mixture of electrolyzed manganese dioxide (EMD) and V<sub>2</sub>O<sub>5</sub> powder and characterized using cyclic voltammetry (CV), constant current discharge, electrochemical impedance spectroscopy (EIS) and X-ray diffraction technique. CV results showed that VHEMD has a much higher reduction peak current than that of only thermally treated electrolyzed manganese dioxide (HEMD), though both have a similar reduction potential. Constant current discharge measurements showed VHEMD exhibits an improved high rate discharge performance. VHEMD reaches a maximum discharge capacity of 202 mAh g<sup>-1</sup> at a high rate (2 mA cm<sup>-2</sup>), which is considerably higher than that of HEMD (155 mAh g<sup>-1</sup>), although both HEMD and VHEMD have similar discharge capacity at a low rate (0.1 mA cm<sup>-2</sup>). EIS results demonstrated that both Li<sup>+</sup> insertion resistance (R<sub>ct</sub>) and Li<sup>+</sup> diffusion impedance (W) in VHEMD were always lower than those of HEMD at any depth of discharge (DOD). XRD results confirmed that V-doping leads to an anisotropic expansion of MnO<sub>2</sub> lattice, with *a* axis slightly elongated by 0.74% and *c* axis slightly shortened by 0.17%. The improved crystal structure after V-doping can be attributed to the faster kinetics of both Li<sup>+</sup> insertion and diffusion in VHEMD.

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**Keywords:** Li/MnO<sub>2</sub> primary battery, electrolyzed manganese dioxide, V-doped, High rate discharge performance

### 1. INTRODUCTION

With the advantages of low cost, environmentally friendliness and high energy density, Li/MnO<sub>2</sub> primary battery, as one of the most important primary batteries, has been widely used in low power consumption applications, for example power supply for computer motherboards and accutrans. However the poor high rate discharge performance prevents their high power output applications, e.g. the military communicative devices and civil smart meters [1, 2]. It has been proved that both the

electrochemical reaction of Li and the conductivity of electrolyte are suitable for high rate discharge applications. Therefore MnO<sub>2</sub> cathodes are the limiting factor for high rate performance in Li/MnO<sub>2</sub> primary batteries. The conventional cathode active material in Li/MnO<sub>2</sub> primary batteries is thermally treated electrolyzed manganese dioxide (HEMD), which is a mixture of pyrolusite-MnO<sub>2</sub> (*p*-MnO<sub>2</sub>, 65-85 wt%) and ramsdellite-MnO<sub>2</sub> (*r*-MnO<sub>2</sub>) [3, 4]. Under a low power output condition (25 °C, 0.1 mA cm<sup>-2</sup>), the discharge capacity of HEMD can reach 90% for the theoretical capacity of MnO<sub>2</sub>. However, at a high discharge rate, i.e. 25 °C and 2 mA cm<sup>-2</sup>, the discharge capacity remarkably decreases to only 55% of the theoretical capacity. In past decades, a large amount of efforts have been attempted to improve the high rate discharge performance of MnO<sub>2</sub> cathodes. An improved high rate discharge performance can be achieved by reducing the electrode thickness [5, 6] and improving the porosity [5] through cathode structural modification. However the energy density of battery is sacrificed to some extent. Additionally, conductive additives (such as Ag [7], carbon [8, 9]), or preprocessing MnO<sub>2</sub> in O<sub>2</sub>/Air atmosphere [10, 11, 12], only show very limited improvements.

Regarding the discharge process in Li/MnO<sub>2</sub> batteries, Li<sup>+</sup> ions first insert into MnO<sub>2</sub> lattice across the MnO<sub>2</sub>/electrolyte interface and then diffuse within MnO<sub>2</sub> lattice to produce Li<sub>x</sub>MnO<sub>2</sub> (x=0~1) complexes. Apparently, HEMD can satisfy a moderate insertion and diffusion velocity at a low discharge rate. However the nature of slow Li<sup>+</sup> ions insertion and diffusion kinetics within MnO<sub>2</sub> lattice restricts high rate discharge performance of MnO<sub>2</sub> cathodes due to the high electrochemical polarization caused by a high rate discharge current density. Since the slow Li<sup>+</sup> ions insertion/diffusion kinetics in HEMD cathode is the determining factor that confines the high rate electrochemical performance, ameliorating the lattice feature of MnO<sub>2</sub> in HEMD to facilitate Li<sup>+</sup> ions insertion and diffusion properties could be an effective method to improve the high rate performance of Li/MnO<sub>2</sub> batteries. It has already been reported that, doping vanadium into spinal LiMn<sub>2</sub>O<sub>4</sub> materials can improve the electrochemical performance of rechargeable LiMn<sub>2</sub>O<sub>4</sub> batteries [13]. Therefore one could expect that V-doping could also affect the HEMD lattice parameters and hence achieve better Li<sup>+</sup> ions insertion and diffusion kinetics.

In this paper, we attempted to synthesize V-doped HEMD (VHEMD) by thermally treating the mixture of V<sub>2</sub>O<sub>5</sub> and electrolyzed manganese dioxide (EMD, MnO<sub>2</sub> content of EMD sample is 91%). Indeed, VHEMD exhibits a remarkably improved high rate discharge capacity in comparison with conventional HEMD.

## 2. EXPERIMENTAL

The mixture of EMD (Xiangtan, China, 98 wt%) and V<sub>2</sub>O<sub>5</sub> (AR, 2 wt%) was first mechanical ball milled for 20 minutes and then thermally treated at 375 °C for 10 h in an air flow to yield VHEMD. The Mn:V ratio within VHEMD was identified to be 50:1 using ICP-MS (Thermo Electron X7 ICP-MS, USA) element analysis. HEMD was prepared by processing only EMD through exactly the same procedure. VHEMD or HEMD was then mixed entirely with graphite and acetylene black at a weight ratio of 85:7.5:7.5. Then 1.762 g of resulting mixture (either VHEMD or HEMD mixture) was stirred in 100 g of polyvinylidene fluoride (5 wt%) / N-methyl pyrrolidone solution for 10 minutes

to generate a slurry. The slurry was coated onto a thin aluminum foil with a thickness of 0.15  $\mu\text{m}$ . After dried at 105  $^{\circ}\text{C}$  under vacuum for 12 h, they were chopped into either square or round-shaped electrodes. Before any electrochemical measurements, all of these electrodes were further dried at 200  $^{\circ}\text{C}$  under vacuum for 12 h. Round-shaped electrodes with a diameter of 15 mm and a thickness of 60  $\mu\text{m}$  were assembled into test cells (2025) using a lithium negative electrode and a Cegard2400 separator. Square electrodes, with an area of with 0.04  $\text{mm}^2$ , were employed as a working electrode in a three-electrode system with lithium foil as both the reference electrode and counter electrode. Both test cells and three-electrode systems were assembled in Ar atmosphere using 1 M  $\text{LiClO}_4$ : PC: DME (volume ratio of PC to DME is 1:1) as electrolyte.

Constant current discharge measurements were performed on a RT-F Battery Analyser (Luhua, China) with a current density of 0.1 or 2  $\text{mA cm}^{-2}$  at 25  $^{\circ}\text{C}$  respectively. The cut-off voltage was set to be 2.0 V. Both cyclic voltammetry (CV) and electrochemical impedance spectroscopy (EIS) were performed on a CHI660C electrochemical workstation (CHI, China). The CV was carried out in a potential range of 3.2-1.0 V with scan rates of 0.05, 0.25, 0.50 and 1.00  $\text{mV s}^{-1}$  respectively. The amplitude of the AC signal for EIS was set at 5 mV and the frequency was ranged from  $10^{-2}$  to  $10^5$  Hz. A X'pert PRO DY2198 X-ray powder diffractometer (PANalytical, Netherlands) was employed to characterize the crystal structures of HEMD and VHEMD (Cu  $K\alpha$  radiation,  $10^{\circ}$ - $90^{\circ}$ ).

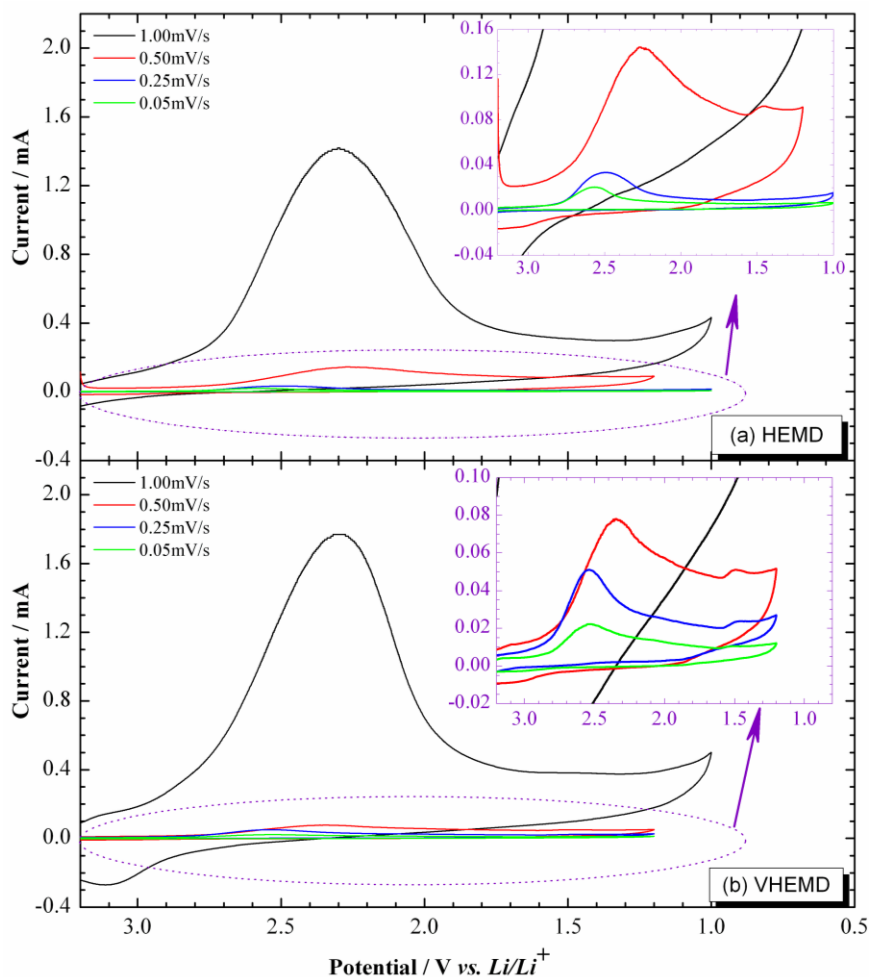
### 3. RESULTS AND DISCUSSION

Fig. 1 shows the CV curves of HEMD and VHEMD at different scan rates. The reduction peak potential of VHEMD appears around 2.3 V at a fast scan rate (1  $\text{mV s}^{-1}$ ) and shifts to an anodic direction with the decrease of scan rate, around 2.57 V at a scan rate of 0.05  $\text{mV s}^{-1}$ . The CV feature of HEMD shows some similarity to that of VHEMD with the reduction peaks positioning in the range of 2.3-2.6 V. Both HEMD and VHEMD exhibit only one reduction peak without any oxidation peak in our experimental scope, which is in consistent with the typical single electron reduction mechanism of  $\text{MnO}_2$  [14]. It can thus be concluded that the V-doping does not change the electrochemical reaction mechanism in  $\text{MnO}_2$  cathode materials. However the reduction peak current of VHEMD is obviously higher than that of HEMD at the same scan rate, indicating that the diffusion and insertion of  $\text{Li}^+$  ions is remarkably improved in VHEMD. Based on their CV data, the apparent electron transfer rate constants  $k_0$  [15] in both VHEMD and HEMD are estimated.

$$I_p = 0.227nFAC_0k_0 e^{\left[-\frac{\alpha F}{RT}(E_p - E^0)\right]}$$

Where  $I_p$  is the peak current of the cathodic  $\text{MnO}_2$  reaction,  $E_p$  is the peak potential,  $n$  is the electrons in the reaction,  $A$  is the area of the electrode,  $C_0$  is the initial concentration of reactants,  $\alpha$  is the transfer coefficient,  $E^0$  is the apparent potential of electrode. The  $k_0$  of VHEMD ( $3.82 \times 10^{-12} \text{ cm s}^{-1}$ ) is 1.7 times greater than that of HEMD ( $2.25 \times 10^{-12} \text{ cm s}^{-1}$ ), suggesting that the V-doping improves

the tunnel structures in  $\text{MnO}_2$  and consequently facilitates the electrochemical reduction process of  $\text{MnO}_2$ . Thus an improved high rate discharge property can be expected in VHEMD in comparison with conventional HEMD.

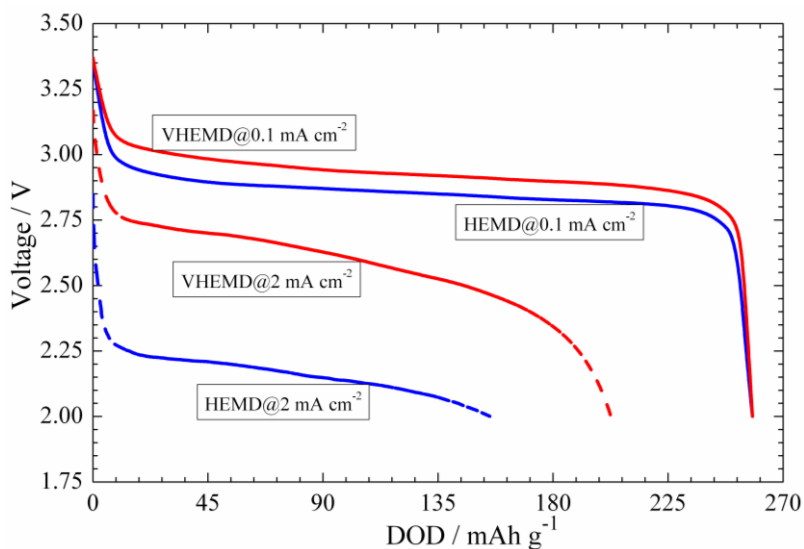


**Figure 1.** The cyclic voltammetric curves of (a) HEMD and (b) VHEMD.

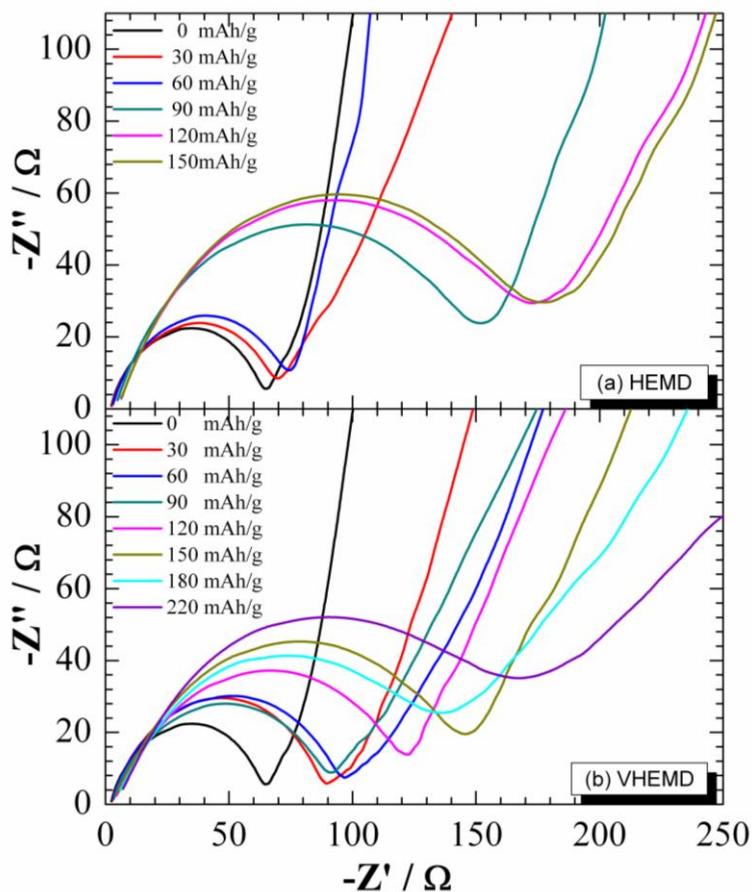
Constant current discharge measurements were conducted within HEMD and VHEMD test cells. Their constant current discharge curves were shown in Fig. 2. The available discharge capacity in both HEMD and VHEMD reaches  $258 \text{ mAh g}^{-1}$  (92% theoretical capacity of  $\text{MnO}_2$ ) at a low rate discharge current density of  $0.1 \text{ mA cm}^{-2}$  with a cut-off voltage of 2.0 V. The only difference is that the discharge plateau of VHEMD is slightly higher than that of HEMD. At a high rate discharge current density ( $2 \text{ mA cm}^{-2}$ ), VHEMD shows a much higher discharge voltage plateau (2.6 V of VHEMD vs. 2.2 V of HEMD). More importantly, the available capacity of VHEMD attains  $202 \text{ mAh g}^{-1}$  (72% of the theoretical capacity), which is considerably higher than that of HEMD ( $155 \text{ mAh g}^{-1}$ ).

Fig. 3 depicts the EIS spectra of both HEMD and VHEMD with different depth of discharge (DOD). These EIS spectra exhibit a typical feature of  $\text{Li}^+$  ions insertion to  $\text{MnO}_2$  lattice in the high frequency region and  $\text{Li}^+$  ions diffusion within  $\text{MnO}_2$  lattice to form nonstoichiometric  $\text{Li}_x\text{MnO}_2$  ( $x=0\sim 1$ ) complexes in the low frequency region. Using the equivalent circuit model (as shown in Fig.

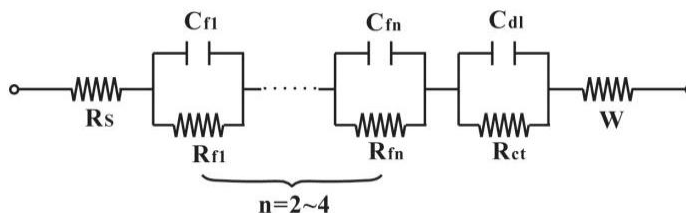
4) proposed by Aurbach et al [16], we obtained the  $\text{Li}^+$  ions insertion resistance ( $R_{ct}$ ) through the liquid-solid interface as shown in Fig. 5(a).



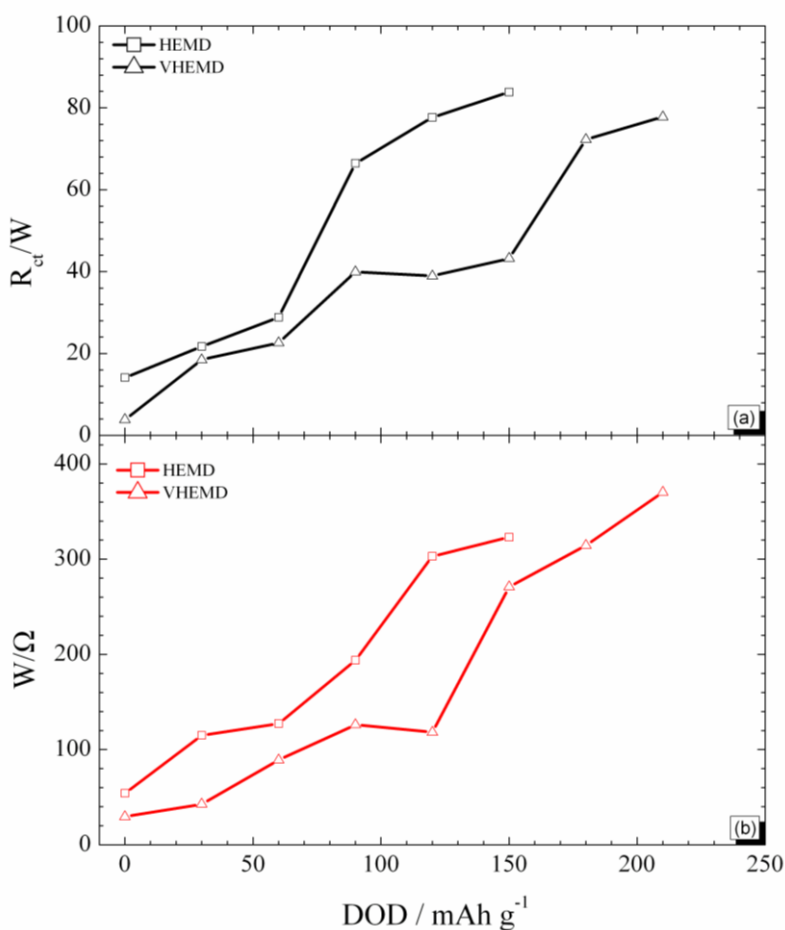
**Figure 2.** The discharge curve of HEMD and VHEMD.



**Figure 3.** EIS spectra of both (a) HEMD and (b) VHEMD at different DODs.



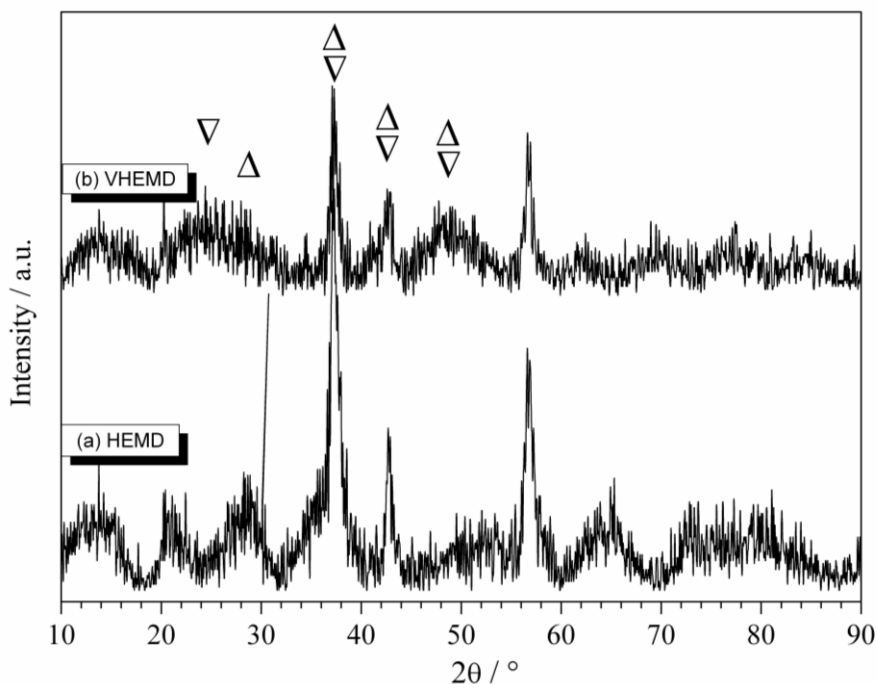
**Figure 4.** The equivalent circuit model for the EIS spectra of both HEMD and VHEMD. Where  $R_s$  is the electrolyte resistance, the impedance of capacitance  $C_{fn(n=2\sim4)}$  and impedance  $R_{fn(n=2\sim4)}$  in parallel is the electrode surface film resistance,  $C_{dl}$  is the double-layer capacitance of the material interface,  $R_{ct}$  is the charge transfer resistance,  $W$  is the diffusion resistance of the  $Li^+$  ions within the  $MnO_2$  lattice.



**Figure 5.** Plots of (a)  $Li^+$  ions insertion impedance ( $R_{ct}$ ) and (b)  $Li^+$  ions diffusion impedance ( $W$ ) vs. depth of discharge.

The  $R_{ct}$  of initial VHEMD cathode is  $3.88 \Omega$  ( $DOD=0$ ), which is remarkably lower than that of HEMD ( $14.14 \Omega$ ). As more and more  $Li^+$  ions insert into the lattice, the  $R_{ct}$  in both HEMD and VHEMD increases simultaneously while the  $R_{ct}$  values in VHEMD are always lower than those of HEMD, implying that VHEMD is capable of providing faster  $Li^+$  ions insertion kinetics than HEMD at any DOD. Also we observed that the  $Li^+$  ions diffusion impedance ( $W$ ) of VHEMD at any DOD is

lower than that of HEMD as shown in Fig. 5(b). Low Warburg impedance means that VHEMD enables a faster  $\text{Li}^+$  ions diffusion process within lattice, which could be the reason why VHEMD reduces the electrochemical polarization and hence exhibit better high rate discharge performance.



**Figure 6.** XRD patterns of (a) HEMD and (b) VHEMD powders, where  $\Delta$  represents pyrolusite and  $\nabla$  represents ramsdellite phases.

In order to understand the structural difference in HEMD and VHEMD, the XRD patterns of both powders are characterized as shown in Fig. 6. Strong peaks of  $p\text{-MnO}_2$  are observed at similar positions in both VHEMD and HEMD, while none of the  $\text{V}_2\text{O}_5$  feature appears in Fig. 6(b). It can be concluded that, through the thermal treatment at 375 °C,  $\text{V}_2\text{O}_5$  has incorporated into  $\text{MnO}_2$  lattice forming a new  $\text{Mn}_x\text{V}_{1-x}\text{O}_2$  ( $x=0\sim 1$ ) binary oxide phase [17, 18]. The calculated lattice parameters for most  $p\text{-MnO}_2$  are listed in Table 1.

**Table 1.** The calculated lattice parameters for  $p\text{-MnO}_2$  of HEMD and VHEMD.

	$a(\text{\AA})$	$c(\text{\AA})$	$v(\text{\AA}^3)$
HEMD	4.3792	2.9021	55.6546
VHEMD	4.4115	2.8971	56.3808

Upon the doping of V, an anisotropic expansion for  $\text{MnO}_2$  lattice occurs. The  $a$  axis is slightly elongated by 0.74% while the  $c$  axis is slightly shortened by 0.17%. The unit cell volume expansion is

calculated to be 1.30%. Since  $\text{Li}^+$  ions insert through the (001) face and diffuse through  $[1 \times 1]$  tunnels along  $c$ -axis of  $p\text{-MnO}_2$  [14], apparently a large  $a$  axis enables the interfacial  $\text{Li}^+$  insertion easier, and also a smaller  $c$  axis facilitates  $\text{Li}^+$  diffusion from the outer sites to inner sites within the lattice of  $p\text{-MnO}_2$ .

#### 4. CONCLUSIONS

We synthesized V-doped  $\text{MnO}_2$  as cathode materials for  $\text{Li/MnO}_2$  primary battery. Due to the anisotropic expansion of  $\text{MnO}_2$  lattice by introducing vanadium,  $[1 \times 1]$  tunnels are expanded and also the  $c$  axis is shortened. Consequently this anisotropic expansion leads to a favorable electrochemical process for  $\text{Li}^+$  ions insertion and diffusion, allowing fast reduction kinetics of  $\text{MnO}_2$ . The discharge capacity of VHEMD is significantly improved to  $202 \text{ mAh g}^{-1}$  at the high rate discharge current density of  $2 \text{ mA cm}^{-1}$  with a cut-off voltage of 2.0 V, compared to  $155 \text{ mAh g}^{-1}$  of HEMD at the same condition. By optimizing the doping rate or using different doping elements, we can further make the high-rate performance reach the maximal capacity for  $\text{MnO}_2$  based  $\text{Li/MnO}_2$  primary batteries. We will report the corresponding results in extended papers in the near future.

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